

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI SD1018-06** is Designed for Class C Amplifier Applications in VHF Mobile Radios.

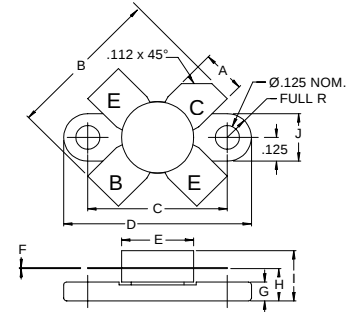
FEATURES:

- $P_G = 4.5$ dB Typ. at 40 W /175 MHz
- $\eta_c = 60\%$ Typ. at 40 W /175 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	6.0 A
V_{CBO}	36 V
V_{CEO}	18 V
V_{EBO}	4.0 V
P_{DISS}	80 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	2.2 $^\circ\text{C/W}$

PACKAGE STYLE .380 4L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 20$ mA	36			V
BV_{CEO}	$I_C = 100$ mA	18			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CBO}	$V_{CB} = 15$ V			2.5	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ A	5.0			---
C_{ob}	$V_{CB} = 15$ V $f = 1.0$ MHz			200	pF
P_G η_c	$V_{CC} = 12.5$ V $P_{OUT} = 40$ W $f = 175$ MHz $P_{IN} = 14$ W	4.5	60		dB %